

PATENT ABSTRACTS OF JAPAN B 28

(11)Publication number : 63-266814
 (43)Date of publication of application : 02.11.1988

(51)Int.Cl. H01L 21/205

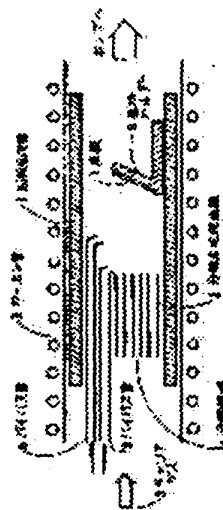
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(54) FORMING METHOD FOR AL III-V COMPOUND SEMICONDUCTOR THIN FILM

(57)Abstract:

PURPOSE: To form an superthin film of Al III-V compound semiconductor by an atomic layer epitaxy by supplying in advance Al organic compound to a decomposing area to decompose the compound, condensing and removing generated sole aluminum, and then supplying the decomposed gas onto a substrate.

CONSTITUTION: A carbon tube 2 is mounted in a quartz reaction tube 1, and set at a predetermined temperature. Hydrogen gas of carrier gas 3 is fed from left to right to transport $Al(C_2H_5)_2Cl$. Carbon decomposition reaction accelerating plates 5 are arranged on a decomposing area 4 at the upstream of a substrate in the tube 2, and a carbon substrate holder 6 for placing the substrate 7 is provided at the downstream of the area. Then, above semiconductor thin film forming apparatus is used to grown AIAs on the substrate, AsH_3 is introduced as group V element gaseous compound through a carbon bypass tube 8 bypassing the decomposing area to the periphery of the substrate. Thus, the extremely thin film of Al III-V compound semiconductor can be formed under good controllability.



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[Date of request for examination]
 [Date of sending the examiner's decision of rejection]
 [Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]
 [Date of final disposal for application]
 [Patent number]
 [Date of registration]
 [Number of appeal against examiner's decision of rejection]
 [Date of requesting appeal against examiner's decision of rejection]
 [Date of extinction of right]